$\label{eq:effects} \mbox{Effects of annealing temperature on Cu_2ZnSnS_4 (CZTS) films formed by an electrospray technique}$

<u>진려평</u>, 김홍탁, 박진호[†] 영남대학교 (chpark@ynu.ac.kr[†])

The electrospray technique is a simple and inexpensive method for producing high-quality Cu_2ZnSnS_4 (CZTS) films under low temperature conditions. The effects of annealing temperature for the as-deposited CZTS films were investigated. All the as-grown CZTS films exhibited a kesterite structure with a preferred orientation of (112), (220) and (312). And there was no phase transition according to annealing temperature. In addition, all samples exhibited a CZTS characteristic peak in the Raman spectra centered at 336 cm⁻¹, which indicated the CZTS phase was established during the film depositions. The grain size of the CZTS films increased substantially in the range of 300 – 450 °C, and the optical band-gap (Eg) of the CZTS films under different annealing temperatures decreased from 1.71 eV to 1.42 eV. The blue shift in Eg was strongly related to the grain size due to the quantum confinement effects. It is found that the annealing process improved the crystallinity and optical properties of the films, making them suitable for photovoltaic applications.